

# Sanjay Krishna

## List of Publications by Year in descending order

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509  
papers

10,367  
citations

38720

50  
h-index

54882

84  
g-index

514  
all docs

514  
docs citations

514  
times ranked

7127  
citing authors

#	ARTICLE	IF	CITATIONS
1	Interband Quantum Cascade Infrared Photodetectors: Current Status and Future Trends. Physical Review Applied, 2022, 17, .	1.5	14
2	Random alloy thick AlGaAsSb avalanche photodiodes on InP substrates. Applied Physics Letters, 2022, 120, .	1.5	17
3	Impact Ionization Coefficients of Digital Alloy and Random Alloy Al <sub>0.85</sub> Ga <sub>0.15</sub> As <sub>0.56</sub> Sb <sub>0.44</sub> in a Wide Electric Field Range. Journal of Lightwave Technology, 2022, 40, 4758-4764.	2.7	10
4	Temperature Dependence of Avalanche Breakdown of AlGaAsSb and AlInAsSb Avalanche Photodiodes. Journal of Lightwave Technology, 2022, 40, 5934-5942.	2.7	6
5	Morphological and optical characterization of self-assembled InAlGaAs/GaAs quantum dots. Journal of Applied Physics, 2022, 131, 233104.	1.1	2
6	Signal and Noise Analysis of an Open-Circuit Voltage Pixel for Uncooled Infrared Image Sensors. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, , 1-14.	3.5	2
7	Plasmonic-coupled quantum dot photodetectors for mid-infrared photonics. Optics Express, 2021, 29, 7145.	1.7	3
8	AlInAsSb avalanche photodiodes on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	31
9	Low noise AlInAsSb avalanche photodiodes on InP substrates for 1.55 $\mu\text{m}$ infrared applications. , 2021, , .		4
10	Thick Al <sub>0.85</sub> Ga <sub>0.15</sub> As <sub>0.56</sub> Sb <sub>0.44</sub> avalanche photodiodes on InP substrate. , 2021, , .		3
11	Investigating the physics of higher-order optical transitions in InAs/GaSb superlattices. Physical Review B, 2021, 104, .	1.1	6
12	Antimonide-Based Avalanche Photodiodes on InP Substrates. , 2021, , .		0
13	Simulation of Impact Ionization Coefficients in InAlAs/InAsSb Type-II Superlattice Material Systems. Journal of Electronic Materials, 2021, 50, 7293.	1.0	1
14	Dielectric Resonator Antenna-Coupled Antimonide-Based Detectors (DRACAD) for the Infrared. IEEE Transactions on Antennas and Propagation, 2021, 69, 6762-6771.	3.1	4
15	Investigation of bulk and surface minority carrier lifetimes in metamorphic InAsSb grown on GaAs and Si. Journal of Applied Physics, 2021, 129, 015106.	1.1	2
16	Low noise Al <sub>0.85</sub> Ga <sub>0.15</sub> As <sub>0.56</sub> Sb <sub>0.44</sub> avalanche photodiodes on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	30
17	Optical constants of Al <sub>0.85</sub> Ga <sub>0.15</sub> As <sub>0.56</sub> Sb <sub>0.44</sub> and Al <sub>0.79</sub> In <sub>0.21</sub> As <sub>0.74</sub> Sb <sub>0.26</sub> . Applied Physics Letters, 2021, 119, .	1.5	8
18	Antimonide-Based Avalanche Photodiodes on InP Substrates. , 2021, , .		0

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19	Photoluminescence spectroscopy of metamorphic InAsSb on GaAs and Si. Journal of Luminescence, 2020, 228, 117581.	1.5	4
20	Multiplication characteristics of Al <sub>0.4</sub> Ga <sub>0.07</sub> In <sub>0.53</sub> As avalanche photodiodes grown as digital alloys on InP substrates. , 2020, , .		0
21	Open-circuit voltage photodetector architecture for infrared imagers. Applied Physics Letters, 2020, 117, .	1.5	5
22	Engineering of impact ionization characteristics in In <sub>0.53</sub> Ga <sub>0.47</sub> As/Al <sub>0.48</sub> In <sub>0.52</sub> As superlattice avalanche photodiodes on InP substrate. Scientific Reports, 2020, 10, 16735.	1.6	12
23	InAsSb-Based Infrared Photodetectors: Thirty Years Later On. Sensors, 2020, 20, 7047.	2.1	46
24	Advancing Uncooled Infrared Imagers Using An Open-Circuit Voltage Pixel. , 2020, , .		1
25	Vertical carrier transport in strain-balanced InAs/InAsSb type-II superlattice material. Applied Physics Letters, 2020, 116, .	1.5	27
26	Determination of background doping polarity of unintentionally doped semiconductor layers. Applied Physics Letters, 2020, 116, .	1.5	4
27	InAs <sup>1-3</sup> ySby virtual substrates grown by MOCVD for long wave infrared detectors. Journal of Crystal Growth, 2020, 535, 125552.	0.7	4
28	Quantum efficiency of plasmonic-coupled quantum dot infrared photodetectors for single- color detection: the upper limit of plasmonic enhancement. Optics Express, 2020, 28, 7618.	1.7	3
29	Phonon-polaritons: enabling powerful capabilities for infrared photonics. Nanophotonics, 2019, 8, 2129-2175.	2.9	113
30	Measurement of carrier lifetime in micron-scaled materials using resonant microwave circuits. Nature Communications, 2019, 10, 1625.	5.8	12
31	Temperature-Dependent Minority-Carrier Mobility in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$	1.5	13
32	Investigation of carrier localization in InAs/AlSb type-II superlattice material system. Applied Physics Letters, 2019, 115, .	1.5	10
33	Photodetector Architecture for Open Circuit Voltage Operation of MWIR InAsSb Detectors. , 2019, , .		2
34	Carrier concentration and transport in Be-doped InAsSb for infrared sensing applications. Infrared Physics and Technology, 2019, 96, 184-191.	1.3	5
35	Photoluminescence study of InAs/InGaAs sub-monolayer quantum dot infrared photodetectors with various numbers of multiple stack layers. Journal of Luminescence, 2019, 207, 512-519.	1.5	18
36	Subwavelength antimonide infrared detector coupled with dielectric resonator antenna. , 2019, , .		6

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37	Temperature-dependent minority carrier lifetime in InAsSb nBn detectors on alternative substrates. , 2019, , .		4
38	RF Read-Out of Minority Carrier Lifetimes in Micro-Scale Infrared Materials. , 2019, , .		0
39	Low noise, near-infrared APDs for laser wavefront monitoring. , 2019, , .		0
40	Novel photodetector design using open circuit voltage for mid-wave infrared imagers. , 2019, , .		2
41	Fabrication of InAs quantum ring nanostructures on GaSb by droplet epitaxy. Journal of Crystal Growth, 2018, 492, 71-76.	0.7	7
42	Photoreflectance study on the photovoltaic effect in InAs/GaAs quantum dot solar cell. Current Applied Physics, 2018, 18, 667-672.	1.1	9
43	Investigation of digital alloyed AlInSb metamorphic buffers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	4
44	Mid-wavelength infrared unipolar nBp superlattice photodetector. Infrared Physics and Technology, 2018, 88, 114-118.	1.3	11
45	Electrical Readout of Carrier Dynamics in Micro-Scale Infrared Materials. , 2018, , .		0
46	Antimonide Based Infrared Detectors for Remote Sensing. , 2018, , .		0
47	Antimonide Based Infrared Detectors and Focal Plane Arrays. , 2018, , .		0
48	Side Wall Passivation of LWIR P-type Superlattice Detectors using Atomic Layer Deposition. , 2018, , .		3
49	Theoretical study of strain-dependent optical absorption in a doped self-assembled InAs/InGaAs/GaAs/AlGaAs quantum dot. Beilstein Journal of Nanotechnology, 2018, 9, 1075-1084.	1.5	2
50	Impact of temperature and gamma radiation on electron diffusion length and mobility in p-type InAs/GaSb superlattices. Journal of Applied Physics, 2018, 123, .	1.1	6
51	Many-body perturbation theory study of type-II InAs/GaSb superlattices within the GW approximation. Journal of Physics Condensed Matter, 2018, 30, 325701.	0.7	8
52	Vertical transport study of InAs/GaSb type-II superlattice nBp MWIR detectors using electron beam-induced current measurements. , 2018, , .		0
53	Carrier concentration and transport in Be-doped InAsSb for infrared sensing applications. , 2018, , .		0
54	InAs/AlSb type II superlattice avalanche photodiodes (Erratum). , 2018, , .		1

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55	Electronic structure modeling of InAs/GaSb superlattices with hybrid density functional theory. <i>Infrared Physics and Technology</i> , 2017, 81, 27-31.	1.3	12
56	Antimonide-based membranes synthesis integration and strain engineering. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2017, 114, E1-E8.	3.3	15
57	Vertical Charge Transfer and Lateral Transport in Graphene/Germanium Heterostructures. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 15830-15840.	4.0	2
58	A novel approach to study the pMDI plume using an infrared camera and to evaluate the aerodynamic properties after varying the time between actuations. <i>International Journal of Pharmaceutics</i> , 2017, 526, 41-49.	2.6	6
59	High quantum efficiency mid-wavelength infrared superlattice photodetector. , 2017, , .		1
60	In situ flashes of gallium technique for oxide-free epitaxial GaSb (100) surface. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, 02B114.	0.6	3
61	Noise, gain, and capture probability of p-type InAs-GaAs quantum-dot and quantum dot-in-well infrared photodetectors. <i>Journal of Applied Physics</i> , 2017, 121, 244501.	1.1	22
62	Detection theory for accurate and non-invasive skin cancer diagnosis using dynamic thermal imaging. <i>Biomedical Optics Express</i> , 2017, 8, 2301.	1.5	42
63	CMOS approach to compressed-domain image acquisition. <i>Optics Express</i> , 2017, 25, 4076.	1.7	3
64	Ultra-thin infrared metamaterial detector for multicolor imaging applications. <i>Optics Express</i> , 2017, 25, 23343.	1.7	66
65	Extraction of minority carrier diffusion length of MWIR Type-II superlattice nBp detector. , 2017, , .		3
66	Intelligent bias-selection method for computational imaging on a CMOS imager. , 2016, , .		0
67	Antimonide Based Mid-Infrared Detectors and Focal Plane Arrays. , 2016, , .		0
68	Comparison of MWIR unipolar barrier structures based on strained layer superlattices (Conference) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5		
69	InAs-QDIP hybrid broadband infrared photodetector. <i>MRS Advances</i> , 2016, 1, 3301-3306.	0.5	0
70	Indium-bump-free antimonide superlattice membrane detectors on silicon substrates. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	13
71	Intelligent bias-selection method for computational imaging on a CMOS imager. , 2016, , .		0
72	Development of dual-band barrier detectors. <i>Proceedings of SPIE</i> , 2016, , .	0.8	6

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73	Frequency-division-multiplexed single-pixel imaging with metamaterials. <i>Optica</i> , 2016, 3, 133.	4.8	23
74	Antimonide superlattice membrane detectors on a silicon substrate. , 2016, , .		1
75	Type-II InAs/GaSb photodiode array pixel isolation by femto-second laser anneal. <i>Infrared Physics and Technology</i> , 2016, 78, 162-166.	1.3	7
76	Single Pixel Quadrature Imaging with Metamaterials. <i>Advanced Optical Materials</i> , 2016, 4, 66-69.	3.6	16
77	Phase 1 Study of Trametinib and Neoadjuvant Chemoradiation (CRT) in Locally Advanced Rectal Cancer (LARC) with KRAS, BRAF, or NRAS Mutations. <i>International Journal of Radiation Oncology Biology Physics</i> , 2016, 96, S107-S108.	0.4	0
78	Oscillatory penetration of near-fields in plasmonic excitation at metal-dielectric interfaces. <i>Scientific Reports</i> , 2016, 6, 24400.	1.6	10
79	Spatio-Temporal Bias-Tunable Readout Circuit for On-Chip Intelligent Image Processing. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2016, 63, 1825-1832.	3.5	7
80	Indium-bump-free antimonide superlattice membrane detectors on a silicon substrates. , 2016, , .		0
81	Band Offsets of III-V and II-VI Materials Studied by Temperature-Dependent Internal Photoemission Spectroscopy. <i>Journal of Electronic Materials</i> , 2016, 45, 4626-4630.	1.0	3
82	Mid-infrared interband cascade photodetectors with high quantum efficiency. , 2016, , .		1
83	Design and Fabrication of a Multispectral Infrared Metamaterial Detector. , 2016, , .		0
84	Mid-infrared metamorphic interband cascade photodetectors on GaAs substrates. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	9
85	InAsSb-based $n$ Bn photodetectors: lattice mismatched growth on GaAs and low-frequency noise performance. <i>Semiconductor Science and Technology</i> , 2015, 30, 105011.	1.0	23
86	Growth of InAs-InAsSb SLS through the use of digital alloys. <i>Journal of Crystal Growth</i> , 2015, 425, 29-32.	0.7	16
87	Progress on the development of interband cascade photodetectors. <i>Proceedings of SPIE</i> , 2015, , .	0.8	0
88	High-operating temperature MWIR unipolar barrier photodetectors based on strained layer superlattices. <i>Proceedings of SPIE</i> , 2015, , .	0.8	2
89	Confocal Raman spectroscopy and AFM for evaluation of sidewalls in type II superlattice FPAs. , 2015, , .		1
90	Mid-infrared materials and devices for $\mu$ W generation infrared imagers. , 2015, , .		0

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91	Investigation of a near mid-gap trap energy level in mid-wavelength infrared InAs/GaSb type-II superlattices. Semiconductor Science and Technology, 2015, 30, 115004.	1.0	15
92	4th generation infrared detectors and focal plane arrays. , 2015, , .		0
93	Quadrature & frequency diverse terahertz imaging with metamaterials. , 2015, , .		0
94	Surface photovoltage spectroscopy study of InAs quantum dot in quantum well multilayer structures for infrared photodetectors. Superlattices and Microstructures, 2015, 88, 711-722.	1.4	8
95	Post-etching mesa surface composition investigation of InAs/GaSb type-II strained layer superlattices using XPS characterization. Infrared Physics and Technology, 2015, 70, 66-69.	1.3	2
96	Photocapacitance study of GaSb: In, As for defect analysis in InAs/GaSb type-II strained layer superlattices. Infrared Physics and Technology, 2015, 70, 40-43.	1.3	1
97	Molecular beam epitaxy growth of antimony-based mid-infrared interband cascade photodetectors. Journal of Crystal Growth, 2015, 425, 364-368.	0.7	7
98	Dark current improvement of the type-II InAs / GaSb superlattice photodetectors by using a gate bias control. Journal of the Korean Physical Society, 2015, 66, 535-538.	0.3	3
99	Radiometric characterization of an LWIR, type-II strained layer superlattice pBiBn photodetector. Infrared Physics and Technology, 2015, 70, 70-75.	1.3	5
100	Reprint of "Mid-infrared InAsSb-based nBn photodetectors with AlGaAsSb barrier layers" grown on GaAs, using an interfacial misfit array, and on native GaSb. Infrared Physics and Technology, 2015, 70, 107-110.	1.3	2
101	InAs/GaAs quantum dot and dots-in-well infrared photodetectors based on p-type valence-band intersublevel transitions. Infrared Physics and Technology, 2015, 70, 15-19.	1.3	17
102	Dark current in antimony-based mid-infrared interband cascade infrared photodetectors. Infrared Physics and Technology, 2015, 70, 44-47.	1.3	8
103	Investigation of plasmonic enhancement in a quantum dot-in-a-well structure. Proceedings of SPIE, 2015, , .	0.8	0
104	Pixel isolation in Type-II InAs/GaSb superlattice photodiodes by femto-second laser annealing. Proceedings of SPIE, 2015, , .	0.8	2
105	Mid-Infrared Interband Cascade Photodetectors With Different Absorber Designs. IEEE Journal of Quantum Electronics, 2015, 51, 1-5.	1.0	14
106	Progress towards vertical transport study of proton-irradiated InAs/GaSb type-II strained-layer superlattice materials for space-based infrared detectors using magnetoresistance measurements. Proceedings of SPIE, 2015, , .	0.8	0
107	Dark current reduction in InAs/InAsSb superlattice mid-wave infrared detectors through restoration etch. Electronics Letters, 2015, 51, 2009-2010.	0.5	9
108	Infrared detectors based on InAs/GaSb superlattice materials (Presentation Recording). , 2015, , .		0

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109	Metamaterial-based single pixel imaging system (Presentation Recording). , 2015, , .		0
110	Modelling of current-voltage characteristics of infrared photo-detectors based on type II InAs/GaSb super-lattice diodes with unipolar blocking layers. AIP Advances, 2015, 5, .	0.6	8
111	MWIR unipolar barrier photodetectors based on strained layer superlattices. Proceedings of SPIE, 2015, , .	0.8	0
112	Dynamic infrared imaging for skin cancer screening. Infrared Physics and Technology, 2015, 70, 147-152.	1.3	38
113	InAs/GaSb Type-II Superlattice for Radiation Thermometry. IEEE Transactions on Instrumentation and Measurement, 2015, 64, 502-508.	2.4	6
114	Dual color longwave InAs/GaSb type-II strained layer superlattice detectors. Infrared Physics and Technology, 2015, 70, 93-98.	1.3	8
115	nBn T2SLs InAs/GaSb/B-AlGaSb HOT detector for fast frequency response operation. , 2014, , .		1
116	Influence of composition in InAs/GaSb type-II superlattices on their optical properties. Electronics Letters, 2014, 50, 1733-1734.	0.5	11
117	Order-of-magnitude enhancement of intersubband photoresponse in a plasmonic quantum dot system. Optics Letters, 2014, 39, 4454.	1.7	3
118	Large aperture adaptive doublet polymer lens for imaging applications. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2014, 31, 1842.	0.8	7
119	Effect of barrier on the performance of sub-monolayer quantum dot infrared photodetectors. Optical Materials Express, 2014, 4, 198.	1.6	11
120	Two-photon photovoltaic effect in gallium arsenide. Optics Letters, 2014, 39, 5297.	1.7	11
121	Simulation and analysis of grating-integrated quantum dot infrared detectors for spectral response control and performance enhancement. Journal of Applied Physics, 2014, 115, .	1.1	2
122	High operating temperature interband cascade focal plane arrays. Applied Physics Letters, 2014, 105, .	1.5	30
123	Study of valence-band intersublevel transitions in InAs/GaAs quantum dots-in-well infrared photodetectors. Applied Physics Letters, 2014, 104, .	1.5	11
124	A novel readout circuit for on-sensor multispectral classification. , 2014, , .		2
125	MWIR superlattice detectors integrated with substrate side-illuminated plasmonic coupler. Proceedings of SPIE, 2014, , .	0.8	3
126	Mid-wave infrared interband cascade photodetectors and focal plane arrays. , 2014, , .		2

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127	Graphene nano-objects tailored by interference lithography. Proceedings of SPIE, 2014, , .	0.8	0
128	Coded and compressive THz imaging with metamaterials. Proceedings of SPIE, 2014, , .	0.8	1
129	High operating temperature midwave infrared (MWIR) photodetectors based on type II InAs/GaSb strained layer superlattice. Proceedings of SPIE, 2014, , .	0.8	3
130	Adaptive polymer lens for rapid zoom shortwave infrared imaging applications. Optical Engineering, 2014, 53, 1.	0.5	5
131	Mid-wavelength infrared type-II InAs/GaSb superlattice interband cascade photodetectors. Optical Engineering, 2014, 53, 043107.	0.5	28
132	Passivation of long-wave infrared InAs/GaSb superlattice detectors with epitaxially grown ZnTe. , 2014, , .		3
133	Investigation of quantum efficiency in mid-wave infrared (MWIR) InAs/GaSb type-II strained layer superlattice (T2SL) detectors. Proceedings of SPIE, 2014, , .	0.8	0
134	Polarization-dependent photocurrent enhancement in metamaterial-coupled quantum dots-in-a-well infrared detectors. Optics Communications, 2014, 312, 31-34.	1.0	13
135	Model-Based Edge Detector for Spectral Imagery Using Sparse Spatiospectral Masks. IEEE Transactions on Image Processing, 2014, 23, 2315-2327.	6.0	4
136	High temperature terahertz response in a p-type quantum dot-in-well photodetector. Applied Physics Letters, 2014, 105, 151107.	1.5	10
137	Carrier lifetime studies in midwave infrared type-II InAs/GaSb strained layer superlattice. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	40
138	Terahertz compressive imaging with metamaterial spatial light modulators. Nature Photonics, 2014, 8, 605-609.	15.6	676
139	Mid-infrared InAsSb-based nBn photodetectors with AlGaAsSb barrier layers “Grown on GaAs, using an interfacial misfit array, and on native GaSb. Infrared Physics and Technology, 2014, 67, 210-213.	1.3	11
140	Passivation techniques for InAs/GaSb strained layer superlattice detectors. Laser and Photonics Reviews, 2013, 7, 45-59.	4.4	42
141	Optical properties of nonpolar III-nitrides for intersubband photodetectors. Journal of Applied Physics, 2013, 113, .	1.1	34
142	Electron barrier study of mid-wave infrared interband cascade photodetectors. Applied Physics Letters, 2013, 103, .	1.5	15
143	Surface Charge Transfer Doping of III“V Nanostructures. Journal of Physical Chemistry C, 2013, 117, 17845-17849.	1.5	19
144	Selective InAs/GaSb strained layer superlattice etch stop layers for GaSb substrate removal. Applied Physics A: Materials Science and Processing, 2013, 111, 671-674.	1.1	4

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145	Broadband enhancement of infrared photodetectors with metamaterial resonators. , 2013, , .		0
146	Dual-band pBp detectors based on InAs/GaSb strained layer superlattices. Infrared Physics and Technology, 2013, 59, 28-31.	1.3	5
147	Fourâ€Color Metamaterial Absorber THz Spatial Light Modulator. Advanced Optical Materials, 2013, 1, 905-909.	3.6	84
148	Investigation of thermal interdiffusion in InAs/In <sub>0.15</sub> Ga <sub>0.85</sub> As/GaAs quantum dot-in-a-well heterostructures. Journal of Luminescence, 2013, 143, 96-100.	1.5	9
149	Type-II InAs/GaSb strained layer superlattices grown on GaSb (111)B substrate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C123.	0.6	6
150	InAs/GaAs <i>p</i>-type quantum dot infrared photodetector with higher efficiency. Applied Physics Letters, 2013, 103, .	1.5	43
151	Hetero-engineering infrared detectors with type-II superlattices. Proceedings of SPIE, 2013, , .	0.8	1
152	MWIR type-II InAs/GaSb superlattice interband cascade photodetectors. , 2013, , .		4
153	Radiation tolerance of type-II strained layer superlattice-based interband cascade infrared photodetectors (ICIP). Proceedings of SPIE, 2013, , .	0.8	1
154	High-operating-temperature MWIR detectors using type II superlattices. Proceedings of SPIE, 2013, , .	0.8	2
155	Low-frequency noise in type-II superlattice MWIR nBn detector. , 2013, , .		4
156	Electron Transport in InAsSb-Based nBn Photodetector Structures. IEEE Transactions on Electron Devices, 2013, 60, 510-512.	1.6	3
157	Performance of mid-wave T2SL detectors with heterojunction barriers. Infrared Physics and Technology, 2013, 59, 22-27.	1.3	28
158	Band engineered HOT midwave infrared detectors based on type-II InAs/GaSb strained layer superlattices. Infrared Physics and Technology, 2013, 59, 72-77.	1.3	21
159	Multi-stack InAs/InGaAs sub-monolayer quantum dots infrared photodetectors. Applied Physics Letters, 2013, 102, 011131.	1.5	73
160	Photovoltaic operation of quantum dot quantum cascade detector with low photoconductive gain for midwave infrared photodetection. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 756-760.	0.8	0
161	High quality interfaces of InAs-on-insulator field-effect transistors with ZrO <sub>2</sub> gate dielectrics. Applied Physics Letters, 2013, 102, .	1.5	33
162	High Operating Temperature Midwave Infrared InAs/GaSb Superlattice Photodetectors on (111) GaSb Substrates. IEEE Electron Device Letters, 2013, 34, 426-428.	2.2	4

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163	Low-dark current structures for long-wavelength Type-II strained layer superlattice photodiodes. Proceedings of SPIE, 2013, , .	0.8	3
164	Barrier Engineered Infrared Photodetectors Based on Type-II InAs/GaSb Strained Layer Superlattices. IEEE Journal of Quantum Electronics, 2013, 49, 211-217.	1.0	36
165	Metamaterial-based imaging for potential security applications. , 2013, , .		2
166	Quantum-engineered mid-infrared type-II InAs/GaSb superlattice photodetectors for high temperature operations. Proceedings of SPIE, 2013, , .	0.8	1
167	(111) InAs/GaSb type-II strained layer superlattice material for high operating temperature detection. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 748-751.	0.8	2
168	nAnalysis of subwavelength metal hole array structure for the enhancement of back-illuminated quantum dot infrared photodetectors. Optics Express, 2013, 21, 4709.	1.7	20
169	Noise spectrum measurements of a midwave, interband cascade infrared photodetector with 33 nm wide electron barrier. Proceedings of SPIE, 2013, , .	0.8	3
170	Modeling of midwavelength infrared InAs/GaSb type II superlattice detectors. Optical Engineering, 2013, 52, 061307.	0.5	15
171	Uncooled MWIR InAs/GaSb type-II superlattice grown on a GaAs substrate. , 2013, , .		5
172	Mid-infrared InAs <sub>0.79</sub> Sb <sub>0.21</sub> -based $nBn$ photodetectors with Al <sub>0.9</sub> Ga <sub>0.2</sub> As <sub>0.1</sub> Sb <sub>0.9</sub> barrier layers, and comparisons with InAs <sub>0.87</sub> Sb <sub>0.13</sub> $p-i-n$ diodes, both grown on GaAs using interfacial misfit arrays. Applied Physics Letters, 2013, 103, .	1.5	50
173	A new CMOS readout circuit approach for multispectral imaging. , 2013, , .		2
174	Mid-wave infrared interband cascade photodetectors and focal plane arrays based on InAs/GaSb superlattices. , 2013, , .		1
175	Spatio-temporal tunable pixels for multi-spectral infrared imagers. , 2013, , .		1
176	Quantum of optical absorption in two-dimensional semiconductors. Proceedings of the National Academy of Sciences of the United States of America, 2013, 110, 11688-11691.	3.3	75
177	Band offsets and carrier dynamics of type-II InAs/GaSb superlattice photodetectors studied by internal photoemission spectroscopy. Applied Physics Letters, 2013, 103, .	1.5	13
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